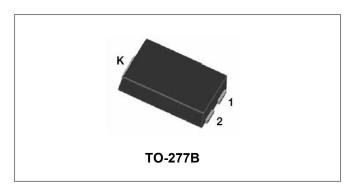






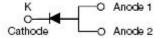
## **MBR15200S SCHOTTKY RECTIFIER**



#### **Features**

- Designed as Bypass Diodes for Solar Panels
- High Forward Surge Capability
- Ultra Low Forward Voltage Drop
- Excellent High Temperature Stability
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	200	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=136°C, rectangular wave form	15	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, Tc=25°C	250	А

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop *	V <sub>F1</sub>	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.85	0.92	V
	V <sub>F2</sub>	@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.72	0.76	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	0.0001	1.0	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	0.1	10	mA
Junction Capacitance	CJ	@V <sub>R</sub> = 5.0 V, Tc=25°C f <sub>SIG</sub> = 1MHz	200	400	pF

<sup>\*</sup> Pulse width < 300  $\mu$ s, duty cycle < 2%

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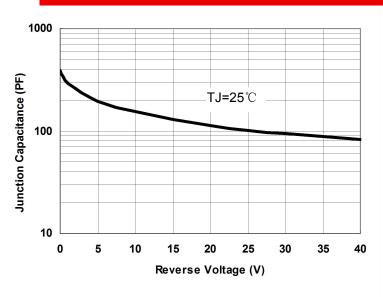




### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +200	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +200	°C
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	25	°C/W
Approximate Weight	wt	-	0.08	g

## **Ratings and Characteristics Curves**



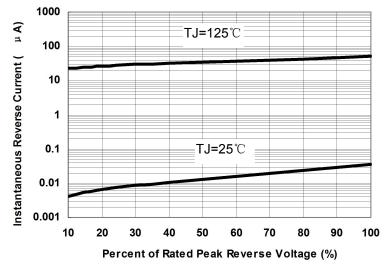


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

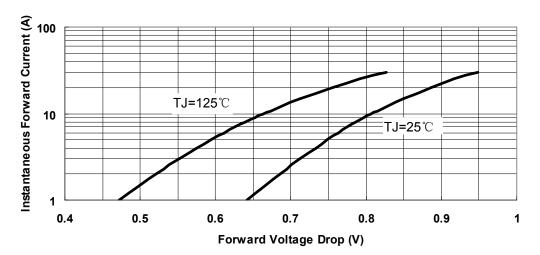


Fig.3-Typical Instantaneous Forward Voltage Characteristics

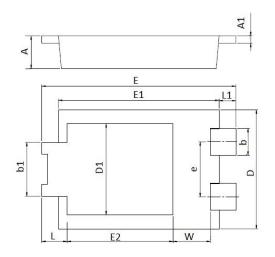
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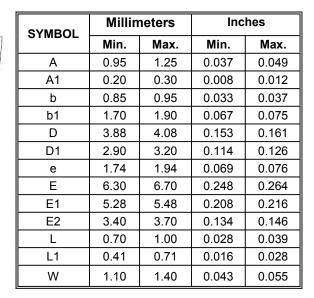






#### **Mechanical Dimensions TO-277B**





#### **Ordering Information**

Device	Package	Shipping
MBR15200S	TO-277B(Pb-Free)	5000pcs/ reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

#### **Marking Diagram**



Where XXXXX is YYWWL

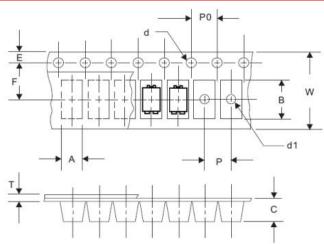
15 = Forward Current (15A) 200 = Reverse Voltage (200V) S = Package type

YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

## Carrier Tape Specification TO-277B



SYMBOL	Millimeters		
STIVIBUL	Min.	Max.	
Α	4.28	4.48	
В	6.80	7.10	
C	1.30	1.50	
d	1.40	1.60	
d1	-	1.50	
Ш	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
Т	0.24	0.44	
W	11.70	12.30	

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